

IN THE SPECIFICATION:

Please amend the paragraph beginning at page 36, line 4, and ending at page 36, line 17, as follows:

--There are no particular prescriptions on the distance between the substrate to be treated and the electrode on the cathode side. With regard to the electrodes for removing the peripheral portion, since a relatively high electric current is flowed thereto, it is preferred that the cathode-side electrode is disposed at a position close to the substrate as far as possible in order to make a loss ~~less~~ occur less and the distance between the electrodes is shorter than that between the electrodes for forming the anti-reflection layer. With regard to the electrodes for forming the anti-reflection layer, the electrode on the cathode side may be at any desired distance to the substrate (see Figs. 13 to 15).--

Please amend the paragraph beginning at page 40, line 3, and ending at page 40, line 10, as follows:

--In the solar cell according to the present invention, the surface of the semiconductor layer may be subjected to texture treatment in order to make incident light ~~less~~ reflect less. In the case of silicon, the treatment is made using hydrazine, NaOH or KOH. The height of pyramids of the texture formed may suitably be within the range of from several microns to tens of microns.--

Please amend the paragraph beginning at page 47, line 12, and ending at page 47, line 25, as follows:

--Next, the wafers with these layers were detached from the jig. On each semiconductor layer and in its region of 75 mm x 75 mm, a comb-like pattern 604 with fingers of 80  $\mu\text{m}$  wide and 100  $\mu\text{m}$  in pitch which extended ~~form~~ from a bus bar of 3 mm wide was formed by screen printing using a paste containing aluminum. Then, the aluminum-silicon contact surface and its vicinity was made into alloy at 900°C to form a p<sup>+</sup>-type layer 605 and simultaneously the whole surface was oxidized. Only the part where silicon surface was oxidized was selectively removed by etching without removing oxide film 606 of aluminum. Thereafter, an n<sup>+</sup>-type semiconductor layer 607 was deposited on the surface by CVD.--